

5      **SINGLE CRYSTAL SILICON SENSOR WITH HIGH ASPECT RATIO  
AND CURVILINEAR STRUCTURES AND ASSOCIATED METHOD**

**ABSTRACT OF THE DISCLOSURE**

10      In one aspect, the invention provides semiconductor sensor which  
SUB CA 7 includes a first single crystal silicon wafer layer. A single crystal silicon  
15 structure is formed in the first wafer layer. The structure includes two  
oppositely disposed substantially vertical major surfaces and two oppositely  
disposed generally horizontal minor surfaces. The aspect ratio of major surface  
to minor surface is at least 5:1. A carrier which includes a recessed region is  
secured to the first wafer layer such that said structure is suspended opposite  
the recessed region.

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